

2SA1282, 2SA1282A

FOR LOW FREQUENCY POWER AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

DESCRIPTION

2SA1282, 2SA1282A is a silicon PNP epitaxial type transistor designed for small type motor drive, solenoid drive and power supply application.

Complementary with 2SC3242, 2SC3242A.

FEATURE

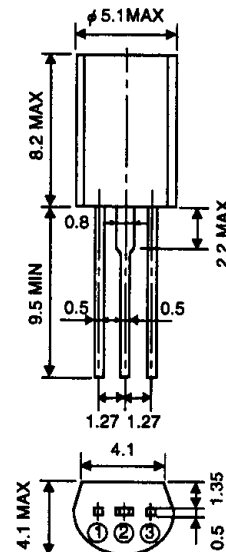
- High collector current $I_C = -2A$
- Low collector saturation voltage
 $V_{CE(sat)} = -0.17V$ typ (@ $I_C = -1A$)
- High $h_{FE} = 150$ to 800
- High collector dissipation $P_C = 900mW$

APPLICATION

VCR, deck, small type motor drive for player, power supply, etc.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : EMITTER
② : COLLECTOR
③ : BASE
- EIAJ : —
JEDEC : —

Note)

The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings		Unit
		2SA1282	2SA1282A	
V _{CB0}	Collector to Base voltage	-20	-20	V
V _{EB0}	Emitter to Base voltage	-6	-6	V
V _{CE0}	Collector to Emitter voltage	-16	-20	V
I _{CM}	Peak collector current	-3		A
I _C	Collector current	-2		A
P _C	Collector dissipation	900		mW
T _J	Junction temperature	+150		°C
T _{stg}	Storage temperature	-55 to +150		°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits						Unit
			2SA1282			2SA1282A			
			Min	Typ	Max	Min	Typ	Max	
V(BR)CBO	C to B break down voltage	I _c = -10 μA, I _E =0	-20			-20			V
V(BR)EBO	E to B break down voltage	I _E = -10 μA, I _c =0	-6			-6			V
V(BR)CEO	C to E break down voltage	I _c = -2 mA, R _{BE} =∞	-16			-20			V
I _c BO	Collector cut off current	V _{CB} = -16 V, I _E =0			-0.2			-0.2	μA
I _E BO	Emitter cut off current	V _{EB} = -4V, I _c =0			-0.2			-0.2	μA
h _{FE} *	DC forward current gain	V _{CE} = -4 V, I _c =-100mA	150		800	150		500	—
V _{CE(sat)}	C to E saturation Voltage	I _c = -1A, I _B = -50mA		-0.17	-0.3		-0.17	-0.3	V
f _r	Gain band width product	V _{CE} = -2V, I _E =10mA		80			80		MHz
C _{ob}	Collector out put capacitance	V _{CB} = -10V, I _E = 0, f=1MHz,		42			42		pF

* : It shows h_{FE} classification in right table.

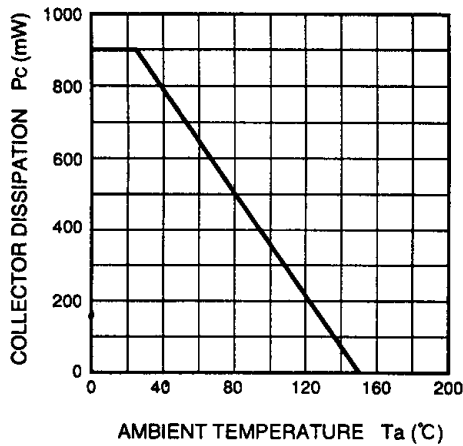
Item	E	F	G
h _{FE}	150 to 300	250 to 500	400 to 800

(SMALL-SIGNAL TRANSISTOR)
2SA1282, 2SA1282A

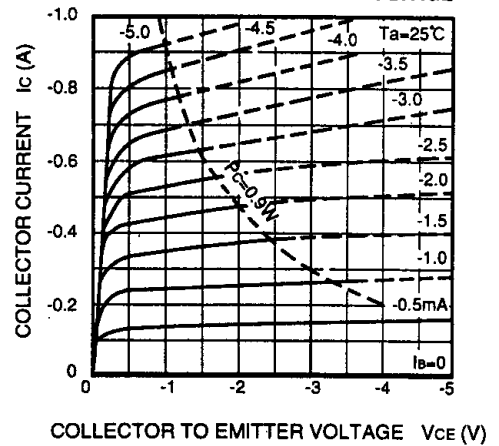
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 SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS

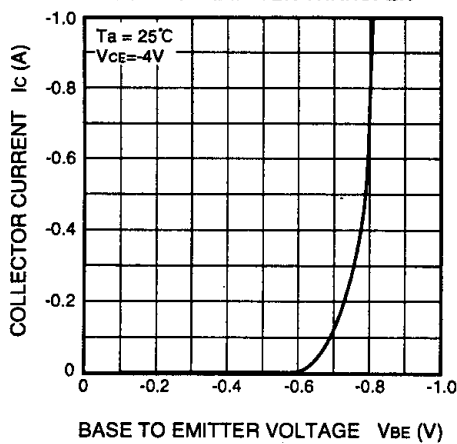
**COLLECTOR DISSIPATION VS.
 AMBIENT TEMPERATURE**



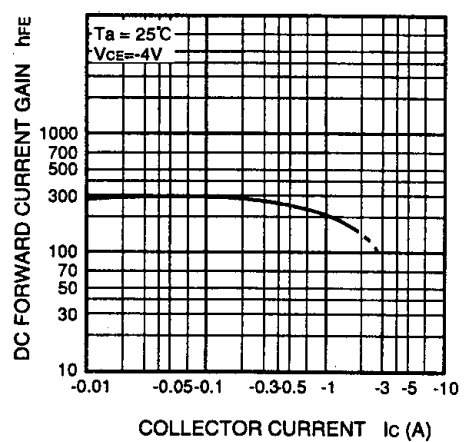
**COMMON EMITTER OUTPUT VS.
 COLLECTOR TO EMITTER VOLTAGE**



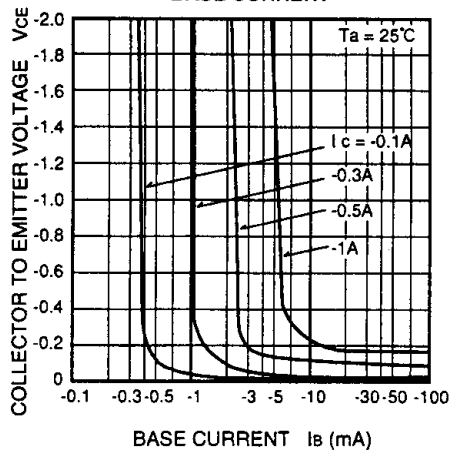
COMMON EMITTER TRANSFER



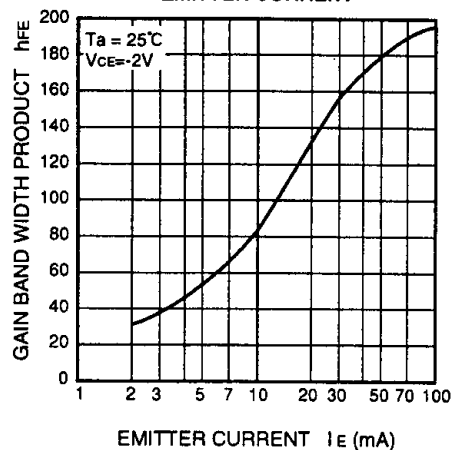
**DC FORWARD CURRENT GAIN VS.
 COLLECTOR CURRENT**

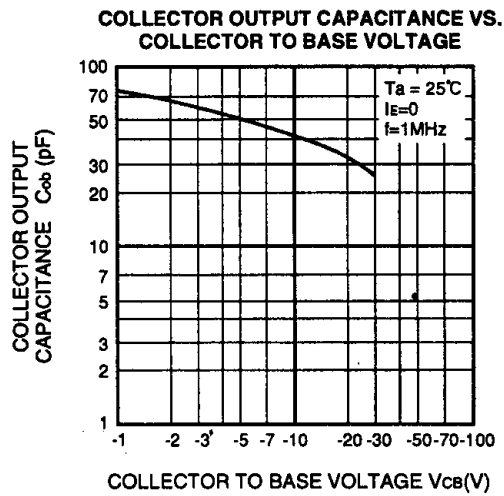


**COLLECTOR TO EMITTER
 SATURATION VOLTAGE VS.
 BASE CURRENT**



**GAIN BAND WIDTH PRODUCT VS.
 EMITTER CURRENT**







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